

## MJE700/701/702/703

### Monolithic Construction With Built-in Base-Emitter Resistors

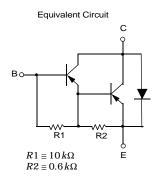
- High DC Current Gain :  $h_{\mbox{\scriptsize FE}}\mbox{\scriptsize =} 750$  (Min.) @  $I_{\mbox{\scriptsize C}}\mbox{\scriptsize =} -1.5$  and -2.0A DC
- Complement to MJE800/801/802/803



## **PNP Epitaxial Silicon Darlington Transistor**

## Absolute Maximum Ratings $T_C=25^{\circ}C$ unless otherwise noted

Sym- bol	Parameter	Value	Unit s
V <sub>CBO</sub>	Collector- Base Voltage : MJE700/701	- 60	V
	: MJE702/703	- 80	V
V <sub>CEO</sub>	Collector-Emitter Voltage: MJE700/701	- 60	V
	: MJE702/703	- 80	V
V <sub>EBO</sub>	Emitter- Base Voltage	- 5	V
I <sub>C</sub>	Collector Current	- 4	Α
I <sub>B</sub>	Base Current	- 0.1	Α
P <sub>C</sub>	Collector Dissipation (T <sub>C</sub> =25°C)	40	W
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature	- 55 ~ 150	°C



### Electrical Characteristics T<sub>C</sub>=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage : MJE700/701 : MJE702/703	I <sub>C</sub> = - 10mA, I <sub>B</sub> = 0	-60 -80		V V
I <sub>CEO</sub>	Collector Cut-off Current : MJE700/701 : MJE702/703	V <sub>CE</sub> = - 60V, I <sub>B</sub> = 0 V <sub>CE</sub> = - 80V, I <sub>B</sub> = 0		-100 -100	μΑ μΑ
I <sub>CBO</sub>	Collector Cut-off Current	$V_{CB}$ = Rated BV <sub>CEO</sub> , $I_E$ = 0 $V_{CB}$ = Rated BV <sub>CEO</sub> , $I_E$ = 0 $T_C$ = 100°C		-100 -500	μA μA
I <sub>EBO</sub>	Emitter Cut-off Current	$V_{BE} = -5V, I_{C} = 0$		-2	mA
h <sub>FE</sub>	DC Current Gain : MJE700/702 : MJE701/703 : ALL DEVICES	$V_{CE} = -3V$ , $I_{C} = -1.5A$ $V_{CE} = -3V$ , $I_{C} = -2A$ $V_{CE} = -3V$ , $I_{C} = -4A$	750 750 100		
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage : MJE700/702 : MJE701/703 : ALL DEVICES	$I_C = -1.5A$ , $I_B = -30mA$ $I_C = -2A$ , $I_B = -40mA$ $I_C = -4A$ , $I_B = -40mA$		-2.5 -2.8 -3	V V V
V <sub>BE</sub> (on)	Base-Emitter On Voltage : MJE700/702 : MJE701/703 : ALL DEVICES	V <sub>CE</sub> = - 3V, I <sub>C</sub> = - 1.5A V <sub>CE</sub> = - 3V, I <sub>C</sub> = - 2A V <sub>CE</sub> = - 3V, I <sub>C</sub> = - 4A		-1.2 -2.5 -3	V V V

# **Typical Characteristics**

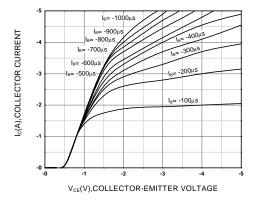


Figure 1. Static Characteristic

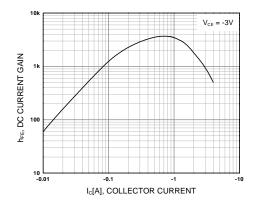


Figure 2. DC current Gain

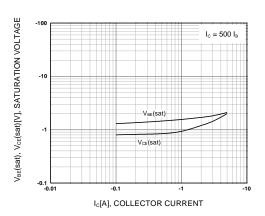


Figure 3. Collector-Emitter Saturation Voltage Base-Emitter Saturation Voltage

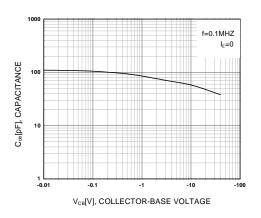


Figure 4. Collector Output Capacitance

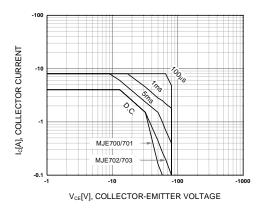


Figure 5. Safe Operating Area

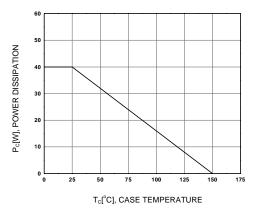
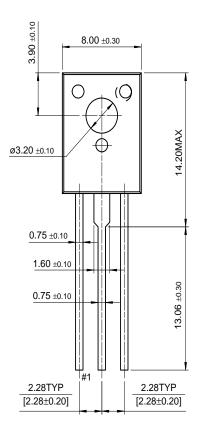


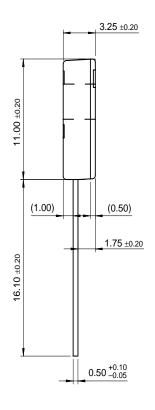
Figure 6. Power Derating

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# **Package Demensions**

TO-126







Dimensions in Millimeters

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